Transition from a fractional quantum Hall liquid to an electron solid at Landau level filling $\nu = 1/3$ in tilted magnetic fields

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We have observed in a low density two-dimensional hole system (2DHS) of extremely high quality (with hole density $p = 1.6 \times 10^{10}$ cm^{-2} and mobility $= 0.8 \times 10^{6}$ cm^2/Vs) that, as the 2DHS is continuously tilted with respect to the direction of the magnetic field, the $\nu = 1/3$ fractional quantum Hall effect (FQHE) state is weakened and its magneto-resistivity rises from 0.4 kΩ/square in the normal orientation to 180 kΩ/square at tilt angle 80°. We attribute this phenomenon to the transition of the 2DHS from the FQHE liquid state to the pinned Wigner solid state, and argue that its origin is the strong coupling of subband Landau levels under the tilted magnetic fields.

The phase transition from a fractional quantum Hall liquid phase[1] to the Wigner solid (WS) phase[2,3] at high magnetic (B) fields or low Landau level fillings (ν) has been a topic of much interest in the study of the two-dimensional electron/hole system (2DES/2DHS)[4]. Experimentally, these two phases show distinctively different temperature (T) dependent behaviors in electronic transport. For the fractional quantum Hall effect (FQHE) state, the magneto-resistivity (ρ_{xx}) becomes vanishingly small when T is much lower than its energy gap (Δ), and increases with increasing temperatures. While for the WS, weakly pinned by residual impurities in real samples, it is an insulator. Consequently, ρ_{xx} decreases with increasing temperatures. Earlier theoretical studies found that the critical transition point depends on the strength of carrier-carrier interaction (characterized by the parameter $r_s = (n\pi)^{-1/2} m^* e^2/4\pi\hbar^2\varepsilon_0\varepsilon$ or $(p\pi)^{-1/2} m^* e^2/4\pi\hbar^2\varepsilon_0\varepsilon$) and moves towards higher n at larger r_s[5] (Here, n (or p) is the 2DES (or 2DHS) density, and other parameters have their usual meanings). For instance, in a high quality 2DES of density $n \sim 1 \times 10^{11}$ cm^{-2}, where $r_s \sim 2$, the WS phase becomes the ground state at the B field above that of $\nu = 1/5$[6]. While in a high quality dilute 2DHS of density $p \sim 5 \times 10^{10}$ cm^{-2}, where $r_s \sim 14$, the DC transport measurements[7] and, especially, the microwave data[8], in which the resonance due to pinning of the WS was discovered at $\nu \sim 0.3$, clearly demonstrated the formation of the WS phase at higher ν in the system of larger r_s.

The magnitude of r_s can be changed by changing the carrier density or changing the 2D system to carriers of a different band mass (m^*). As shown above, with similar carrier densities, r_s in the 2DHS is about 5 times larger than in the 2DES, because of a larger band mass. On the other hand, the method of adding an in-plane magnetic field (B_{ip}), provided by in-situ tilting of the 2D carrier system at low temperatures and in high magnetic fields[9], has not been explored in the experimental studies, while theoretically, it was pointed out[10] recently that a phase transition of the FQHE state from the liquid phase to the Wigner solid phase can be induced by a non-zero B_{ip}. The physical origin behind this phase transition is the effective increase of r_s through the coupling of the Landau levels (or, more accurately, magnetic levels, since the Landau level index is no longer a good quantum number with a non-zero B_{ip}) and 2D subbands (or, the electric levels)[11,12,13]. This Landau level mixing effect reduces the difference between the energies of a FQHE liquid state and the WS state and makes the 2D system effectively more dilute. As a result, the r_s value becomes effectively larger, and a phase transition from a FQHE state to WS can occur. So far, such phase transition has not been identified in experiments.

In this paper, we report the observation of a crossing from the $\nu = 1/3$ FQHE state to an insulating phase in a 2DHS. When tilting the sample with respect to the direction of B field, the $\nu = 1/3$ FQHE state is weakened and at $T \sim 30$ mK its magneto-resistivity (ρ_{xx}) rises from 0.4 kΩ/square in the normal orientation to 180 kΩ/square at the tilt angle 80°. This value is $\sim 7\ h/e^2$, indicating that the $\nu = 1/3$ state is deeply in an insulating phase. We attribute this crossing to the sought-after phase transition from a FQHE state to a weakly pinned Wigner solid state under tilt, and argue that it is caused by the increased r_s value through the coupling of Landau and subband levels.

Our sample consists of a modulation-doped GaAs/$Al_{0.1}Ga_{0.9}As$ quantum well (QW) of 30 nm wide, with silicon δ-doped symmetrically from both sides at a setback distance of 255 nm and grown on the f311gA GaAs substrate. The 2DHS density (p) is $p \sim 1.6 \times 10^{10}$ cm^{-2} and varies about 5% from one cool-down to another. The low-temperature mobility is $\sim 8 \times 10^5$ cm^2/Vsec. The band mass was measured by microwave cyclotron resonance technique and $m^* = 0.35 m_e$[14]. Consequently, r_s in this high quality 2DHS is ~ 23. Ohmic contacts to the 2DHS were made by alloying indium-zinc (In:Zn) mixture at 440 $^\circ$C for 10 minutes in the forming gas. The sample was placed inside the mixing chamber of a dilution refrigerator of base temperature ~ 30 mK (or ~ 60 mK when equipped with a rotating

stage). Sample was tilted in situ from 0 up to 90 with respect to the direction of B . The tilt angle, , was determined from the shift of the resistance minimum of the integer quantum Hall effect (IQHE) states, according to 1/cos( ). Transport measurements of $_{xx}$ and the Hall resistivity $_{xy}$ were carried out using standard low frequency (7 Hz) lock-in techniques with an excitation current of less than 3 nA . Results are reproducible in different cool-downs. No particular effort was made to align B_{ip} with crystallographic directions and current directions.

Fig.1 shows a trace of $_{xx}$ vs. B , taken in the normal orientation. Several features are worth emphasizing: (1) The fully-developed IQHE states at = 1 and 2 and very strong FQHE states at = 1=3 and 2/3 are observed at very small B fields, 2.0 and 1.0 T , respectively, manifesting the high quality of 2DHS in this specimen. We note here that the = 1=3 FQHE state has never been observed and studied at such a low 2D hole density. (2) A $_{xx}$ minimum is seen at = 2=5 and a dip around = 3=5. (3) Between the IQHE states = 1 and 2, there is also a dip at = 5=3. (4) The divergence of $_{xx}$ beyond = 1=3 indicates that the sample is in the insulating regime of the pinned WS phase[7,8]. (5) No reentrant insulating phase is observed between = 2=5 and 1/3 in our sample.

in situ tilting was performed at T 60 mK . In Fig.2, $_{xx}$ traces at seven 's are plotted as a function of perpendicular B field, $B_{perp} = B \cos( )$. It is clearly seen that the = 1=3 state evolves from a well-behaved FQHE state to a strongly insulating state. In details, at small tilt angles, e.g., from 0 to = 33 , the variation of $_{xx}$ is small and = 1=3 is still a good FQHE state (also manifested by the Hall resistance, not shown). Upon further tilting, $_{xx}$ increases considerably. At = 77 , $_{xx}$ 36 k =square and has exceeded $h=e^2$ (26 k =suare), signaling that the 2DHS has entered into an insulating phase. $_{xx}$ continues to increase, to 128 k =square 5 $h=e^2$ at = 80 .

In Fig.3, $_{xx}$ at = 1=3 is plotted as a function of in-plane B field, $B_{ip} = B \sin( )$. Overall, $_{xx}$ (= 1=3) increases exponentially with B_{ip}, i.e., $_{xx}$ (= 1=3) / $\exp(B_{ip}=B_0)$. At T 60 mK , $B_0 = 3{:}6$ T .

In Fig.4, the temperature dependence of $_{xx}$ at = 1=3 is shown on a semilog scale for the seven tilt angles. At = 0 , $_{xx}$ decreases as T decreases from T 200 mK to 60 mK (or 1=T increases from 5 to 16 K^{-1}), the characteristic of a FQHE liquid. From a fit to the linear portion of data, an energy gap of 0:2 K is obtained. The energy gap decreases with increasing and at = 61 , $_{xx}$ is nearly temperature independent, indicating a zero energy gap at = 1=3. When is further increased, on the other hand, $_{xx}$ increases as T decreases, the signature of an insulating phase. In Fig.4b, a linear fit to the higher T data points at = 80 , using the formula $_{xx}$ / $\exp(E_g=2k_B T)$, yields a characteristic energy scale of E_g 0:4 K .

Fig.5 shows the temperature dependence of $_{xx}$ at = 2=3. Similar to the = 1=3 state, the strength of the = 2=3 state shows little changes at small tilt angles. Only when 71 , it becomes weaker, probably the precursor of the same crossing from a FQHE state to an insulator. In contrast, the = 2=5 and 3/5 states disappear quickly at small tilts, becoming indiscernible at = 45 . As for the IQHE states, no weakening of the = 1 and 2 states is observed over the whole tilt range. Finally, it is interesting to note that for the peak at B_{perp} 1:8 T and 0:36, its resistance increases continuously as increases, from 8 k =square at = 0 to 230 k =square at = 80 .

The data in Fig.2 and Fig.4 clearly demonstrate that, as is increased, the = 1=3 state evolves from a FQHE liquid in the normal B field orientation to a hole insulator at high tilt angles. Considering the nature of the strong correlation in its precursor, the = 1=3 FQHE state, and its proximity to the WS phase at yet higher B fields, we assign this hole insulator to the pinned WS phase. This is for the first time that the robust = 1=3 FQHE state is destroyed by the tilted magnetic field and becomes a WS phase at high tilt angles. The lack of such observation in previous experiments indicates that a high quality dilute 2DHS and consequently a large r_s are important for this observation. As to the mechanism for the formation of this tilt induced WS phase, we believe that it is the effective increase of r_s through the coupling of Landau levels and 2D hole subbands under tilt. It is well known that for an ideal 2D system a tilted magnetic field does not modify the orbital motion but only the Zeeman splitting. A real 2D electron system has finite thickness of 10 nm , and the orbital motion is affected only to the second order: The in-plane magnetic field squeezes the electron wavefunction and makes the electron system more two-dimensional. Indeed, the energy gap of the = 1=3 FQHE state was found only to increase slightly[15] with increasing tilt angles. In contrast, for a 2DHS, because of the non-parabolic nature of its valence band and the spin-orbital interaction, in the presence of B_{ip}, the orbital motion is affected greatly and there exists a strong coupling of Landau levels and 2D subbands[16,17,18,19,20]. As pointed out in earlier studies[7,11], Landau level mixing makes the 2D system effectively more dilute and therefore, r_s becomes effectively larger. Consequently, the difference between the energies of a FQHE liquid state and the WS state is reduced[10,11,12,13]. In addition to Landau level mixing, an increment of effective mass m under in-plane B_{ip}[21,22] also directly contributes to increasing r_s, which is proportional to m . Following the previously proposed phase diagram of vs. r_s[5], a crossing from the FQHE state to the WS phase is then possible at = 1=3 by increasing r_s (or the tilt angle), as shown by the arrow in the inset of Fig.2. This evolution can also be viewed as that with increasing r_s the onset of the WS phase moves towards higher . Indeed, in our measurements, the critical transition point ($_c$) from the 2D hole liquid phase to the WS phase, identified as the temperature-independent point in the traces of $_{xx}$ vs. T , moved from $_c$ 0:32 at = 0 to higher as the tilt angle was increased and, at = 80 , $_c$ 0:62, just above the field of the = 2=3 state. Finally, we speculate that the similar mechanism may also be responsible for the transition at the resistance peak of B_{perp} 1:8 T , which was in a metallic phase

($_{xx}$ 8 k =square) at the zero tilt and became an insulator ($_{xx}$ 230 k =square) at large tilt angles.

Next, we notice that even deep in the insulating regime, $_{xx}$ still shows a local minimum at = 1=3, riding on a huge background. The origin of this local minimum may be an indication of the coexistence of the FQHE liquid and the W S. It is known that even in this highest quality 2DHS, residual impurities and density uctuations are inevitable. As a result, the 2DHS may break into domains of liquid and W S. Percolation of the FQHE liquid through the pinned W S can give rise to a local resistance minimum. On the other hand, this resistance dip may be due to electron-electron interactions. It has been shown that the inclusion of the Laughlin-Jastrow correlations in the W igner crystal regime can lower the ground state energy near a rational Landau lling[23]. This energy lowering may also be responsible for the local resistance minimum at = 1=3.

Before we nish the paper, we want to point out that, rstly, the formation of the insulting phase is unlikely caused by the enhanced disorder scattering seen by the 2D holes. It is known that under a non-zero in-plane magnetic eld the e ective mass (m) of the 2D carrier increases and the e ective scattering time decreases. Consequently, the e ective mobility = e =m decreases and the resistivity increases. The increase of m is believed to be due to the coupling of in-plane B eld to the carrier orbital motion[21]. Recently in a two-dimensional electron system, a 20% increase of m was observed[22]. The decrease of is due to the enhanced surface roughness scattering, since under non-zero B_{ip} the 2D hole wavefunction is squeezed and pushed closer to the interface of GaAs=AlGaAs. W e have shown that the coupling e ect is responsible for the observed insulating phase. The enhanced roughness scattering mechanism cannot be the origin of the high tilt insulating phase. In detail, at = 90 , where the 2DHS is expected to experience the maximum interface roughness scattering, a relatively small increase in $_{xx}$, from 0:5 k =square at B = 0 T to 2 k =square at B = 10 T, was measured (as shown in Fig.6). This factor of 4 increase is similar to that at the same density in an earlier theoretical calculation[24], where only the coupling e ect was taken into account. Furthermore, the factor of 4 increase is much smaller than the observed $_{xx}$ increase at = 1=3 from = 0 to = 80 , which is more than two orders of magnitude. Taken these results together, it can be concluded that the enhanced surface roughness scattering is negligible.

Secondly, the increased Zeeman energy in the tilted magnetic eld cannot explain the formation of the insulating phase, either. The non-zero in-plane magnetic eld increases the total magnetic eld seen by the spin, and therefore increases the Zeeman energy. Such a variation in E_Z has been used successfully to interpret the angular dependent disappearance and reappearance of energy gaps of the spin-unpolarized FQHE states, e.g., at = 2=3[25,26,27,28,29,30,31,32,33,34]. However, the ground state of the = 1=3 FQHE state is known to be fully spin-polarized. Thus, all the spins have aligned along the external B eld direction already at zero tilt, and the = 1=3 state should not be a ected and de-stabilized by increasing the Zeeman energy. So far, studies in the 2DES have not identi ed any spin-related phase transitions at = 1/3. Furthermore, the lack of phase transition in $_{xx}$ at = 2=3 also points out that the formation of the insulating phase is not a spin e ect.

To summarize, in this paper, we report experimental results in a 2DHS of density p = 1:6 10^{10} cm ^{2} and mobility = 0:8 10^{6} cm^{2}/Vs in the tilted magnetic elds: The = 1=3 FQHE state was weakened and its magnetoresistivity rose from 0:4 k =square in the normal orientation to 180 k =square at the tilt angle 80 . W e attribute this crossing to a phase transition from a FQHE liquid phase to a pinned W igner solid phase, and argue that this phase transition is due to the e ective increase of r_s value through the strong coupling of subband Landau levels in the presence of non-zero in-plane magnetic elds.

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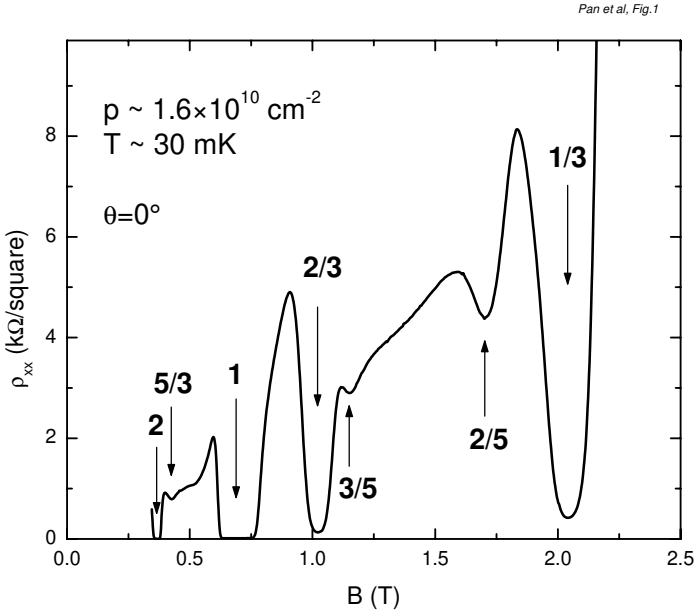

FIG. 1: Overview of $_{xx}$ at = 0. The 2DHS density is p 1:6 10^{10} cm ^{2} and T 30 mK. Major IQHE and FQHE states are indicated by the arrows.

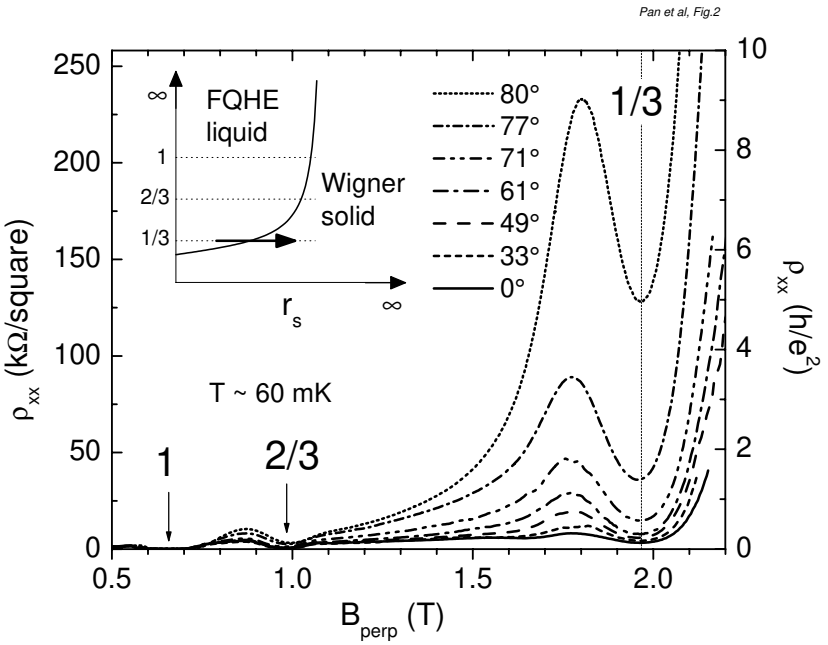

FIG. 2: Tilted B eld dependence of $_{xx}$ at seven angles at = 0 , 33 , 49 , 61 , 71 , 77 , and 80 (from bottom to top). All the traces were taken at T 60 mK, except the one at = 80 , which was taken at T 47 mK. The x-axis is the perpendicular B eld, $B_{perp} = B \cos(\ )$. The right y-axis is in units of $h=e^2$, for the same traces. The inset shows schematically the evolution from a FQHE liquid phase (e.g., at = 1=3) to the WS phase as r_s is increased. This phase diagram is adopted from Ref. [5].

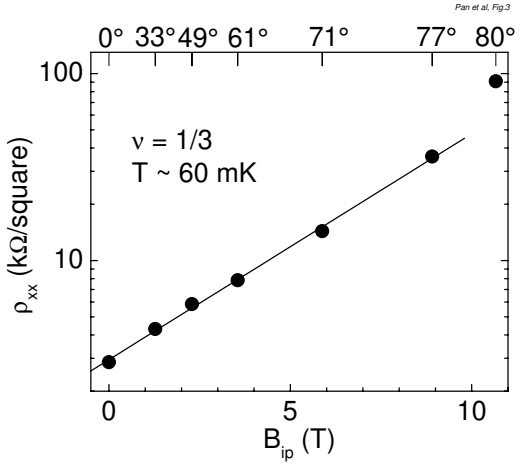

FIG. 3: $_{xx}$ minimum at = 1=3 vs. B_{ip}, plotted on a semi-log scale. The straight line is a linear t to all data points, except the one at = 80 .

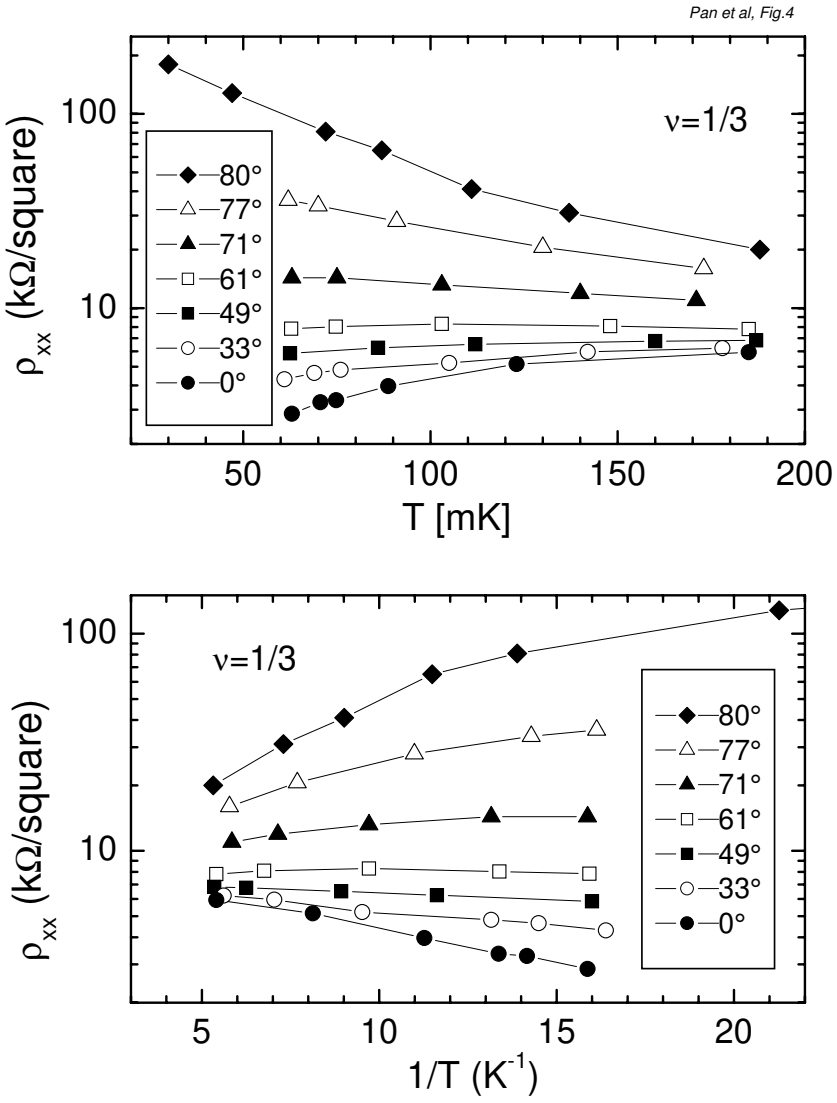

FIG. 4: Temperature dependence of $_{xx}$ minimum at = 1=3 at different tilt angles: (a) $_{xx}$ vs. T; (b) $_{xx}$ vs. 1=T for the same data.

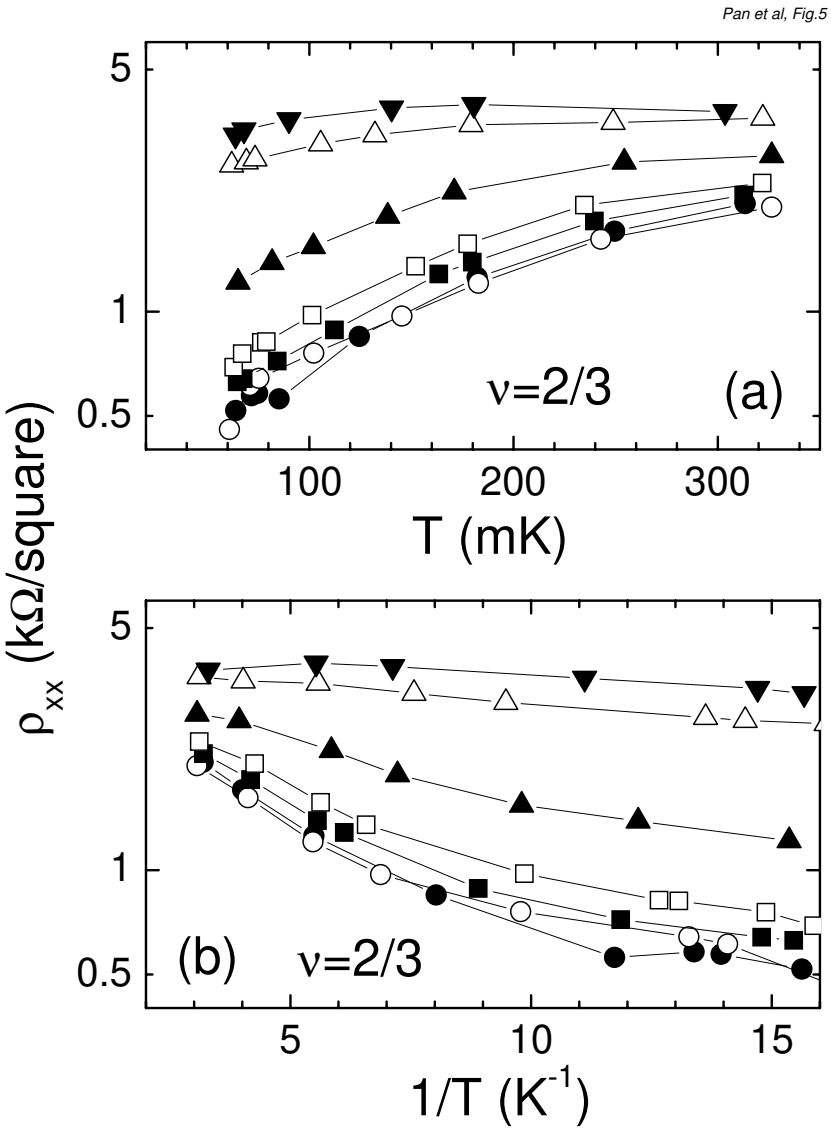

FIG. 5: Temperature dependence of $_{xx}$ minimum at = 2=3 at different tilt angles: (a) $_{xx}$ vs. T; (b) $_{xx}$ vs. 1=T. The same symbol represents the same tilt angle as in Fig.4a and Fig.4b.

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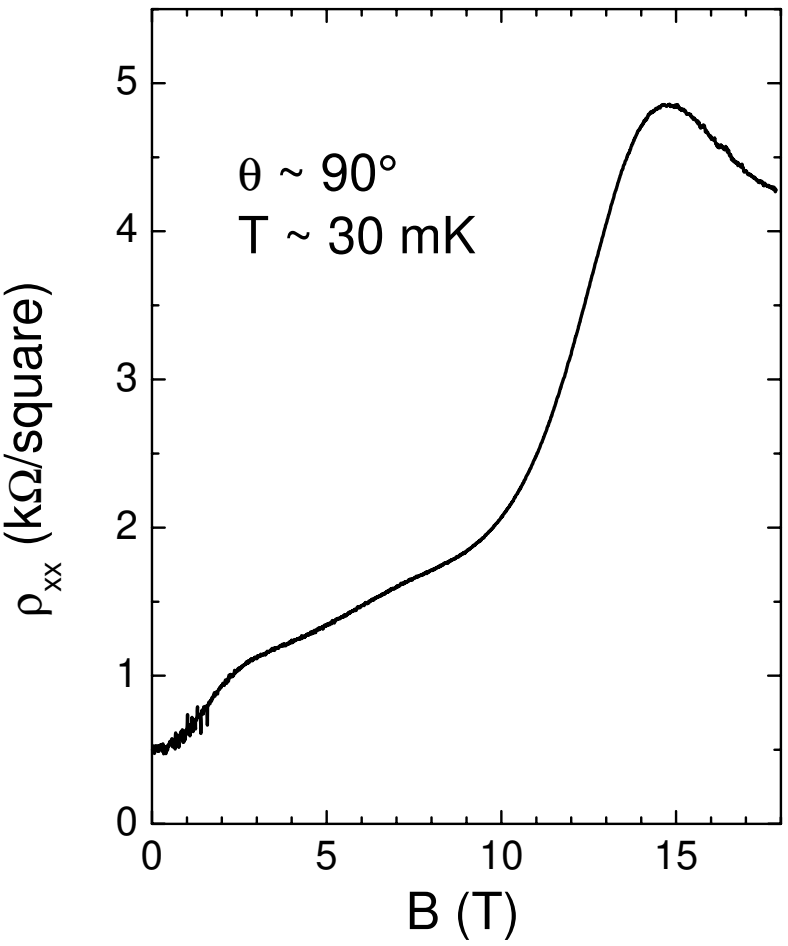

FIG. 6: $_{xx}$ in parallel B eld, 90 .